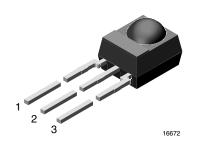
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IR Receiver Module for Light Barrier Systems



MECHANICAL DATA

Pinning:

 $1 = OUT, 2 = GND., 3 = V_S$

FEATURES

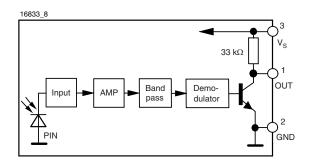
- · Low supply current
- · Photo detector and preamplifier in one package
- Internal filter for 38 kHz IR signals
- · Shielding against EMI
- Supply voltage: 2.7 V to 5.5 V
- · Visible light is suppressed by IR filter
- · Insensitive to supply voltage ripple and noise
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

DESCRIPTION

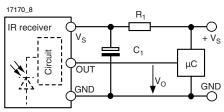
The TSOP4038 is a compact IR receiver for sensor applications. It has a high gain for IR signals at 38 kHz. The detection level does not change when ambient light or strong IR signals are applied. It can receive continuous 38 kHz signals or 38 kHz bursts.

PARTS TABLE					
CARRIER FREQUENCY	SENSOR APPLICATIONS				
38 kHz	TSOP4038				

BLOCK DIAGRAM



APPLICATION CIRCUIT



The external components $R_{_1}$ and $C_{_1}$ are optional to improve the robustnes against electrical overstress (typical values are $R_{_1}=100~\Omega,~C_{_1}=0.1~\mu F).$ The output voltage $V_{_{\rm O}}$ should not be pulled down to a level

below 1 V by the external circuit.

The capacitive load at the output should be less than 2 nF.



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ABSOLUTE MAXIMUM RATINGS (1)								
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT				
Supply voltage (pin 3)		Vs	- 0.3 to + 6.0	V				
Supply current (pin 3)		I _S	5	mA				
Output voltage (pin 1)		Vo	- 0.3 to 5.5	V				
Voltage at output to supply		V _S - V _O	- 0.3 to (V _S + 0.3)	V				
Output current (pin 1)		I _O	5	mA				
Junction temperature		Tj	100	°C				
Storage temperature range		T _{stg}	- 25 to + 85	°C				
Operating temperature range		T _{amb}	- 25 to + 85	°C				
Power consumption	T _{amb} ≤ 85 °C	P _{tot}	10	mW				

Note

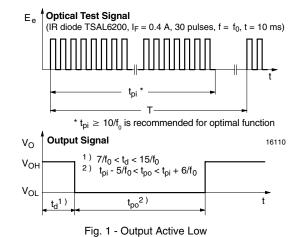
⁽¹⁾ Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating condtions for extended periods may affect the device reliability.

ELECTRICAL AND OPTICAL CHARACTERISTICS (1)									
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Supply current (pin 3)	E _v = 0, V _S = 5 V	I _{SD}	0.65	0.85	1.05	mA			
	$E_v = 40 \text{ klx}$, sunlight	I _{SH}		0.95		mA			
Supply voltage		Vs	2.7		5.5	V			
Transmission distance	E_{v} = 0, test signal see fig. 1, IR diode TSAL6200, I_{F} = 400 mA	d		30		m			
Output voltage low (pin 1)	$I_{OSL} = 0.5 \text{ mA}, E_e = 2 \text{ mW/m}^2,$ test signal see fig. 1	V _{OSL}			100	mV			
Minimum irradiance	Pulse width tolerance: $t_{pi} - 5/f_0 < t_{po} < t_{pi} + 6/f_0,$ test signal see fig. 1	E _{e min.}		0.3	0.7	mW/m ²			
Maximum irradiance	t_{pi} - 5/f _o < t_{po} < t_{pi} + 6/f _o , test signal see fig. 1	E _{e max.}	30			W/m ²			
Directivity	Angle of half transmission distance	Ψ1/2		± 45		deg			

Note

TYPICAL CHARACTERISTICS

T_{amb} = 25 °C, unless otherwise specified



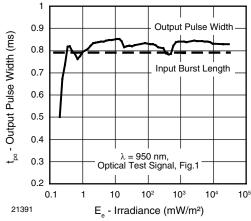


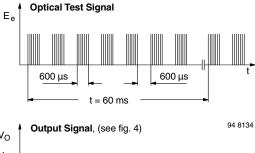
Fig. 2 - Pulse Length and Sensitivity in Dark Ambient

 $^{^{(1)}}$ T_{amb} = 25 $^{\circ}$ C, unless otherwise specified

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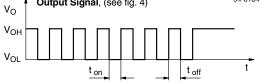


Fig. 3 - Output Function

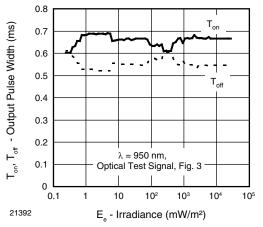


Fig. 4 - Output Pulse Diagram

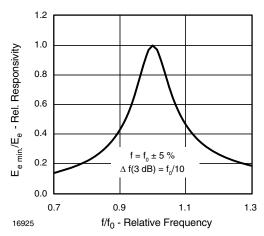


Fig. 5 - Frequency Dependence of Responsivity

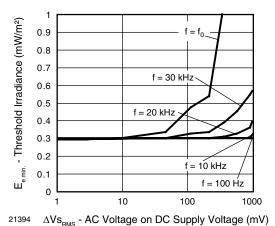


Fig. C. Consistinity on County Valtage Disturbances



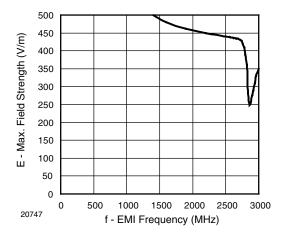


Fig. 7 - Sensitivity vs. Electric Field Disturbances

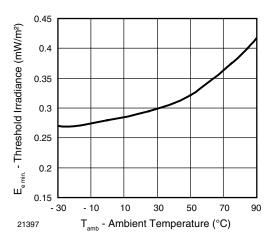


Fig. 8 - Sensitivity vs. Ambient Temperature



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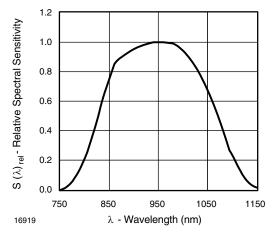


Fig. 9 - Relative Spectral Sensitivity vs. Wavelength

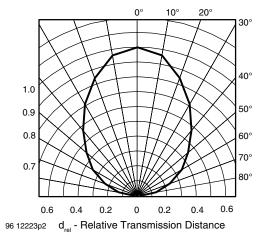


Fig. 10 - Directivity

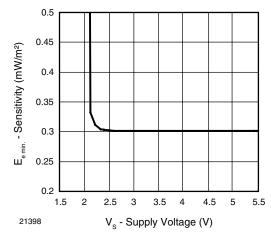


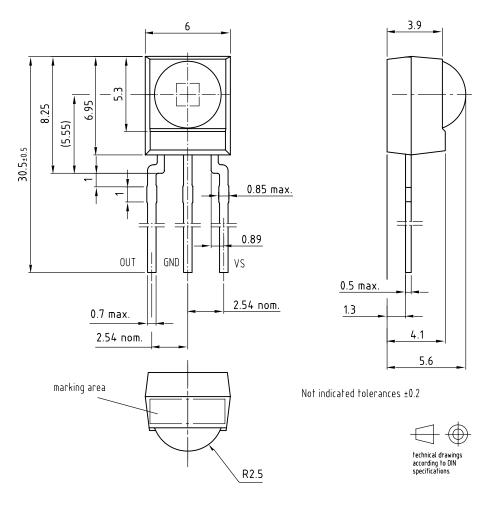
Fig. 11 - Sensitivity vs. Supply Voltage

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PACKAGE DIMENSIONS in millimeters



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OZONE DEPLETING SUBSTANCES POLICY STATEMENT

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA.
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

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